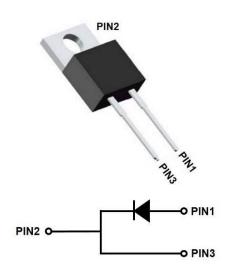




Silicon Carbide Schottky Diode

V_{RRM}	650V
I _{F(135°C)}	9A
Q _C	21.5nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

Package: TO-220AC
 Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free

• Terminals: Tin plated leads

• Polarity: As marked

■Maximum Ratings (T_C=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Device marking code			D106506PYG5
Reverse voltage (Repetitive peak) @ T _j =25°C	V_{RRM}	V	650
Reverse voltage (Surge peak) @ T _j =25°C	V_{RSM}	V	650
Reverse voltage (DC) @ T _j =25°C	V _{DC}	V	650
Continuous forward current @ T _C =25°C			20
Continuous forward current @ T _C =135°C	I _F	Α	9
Continuous forward current @ T _C =156°C			6
Non-repetitive peak forward surge current @ T _C =25°C, tp=10ms, Half Sine Wave	I _{FSM}	А	60
Power Dissipation@ T _C =25°C	D	W	80
Power Dissipation@ T _C =110°C	P _{TOT}		34
i²t Value@ T _C =25°C ,tp=10ms	∫ i²dt	A ² S	18
Operating junction and Storage temperature range	T_{j} , T_{stg}	°C	-55 to +175



YJD106506PYG5

■Electrical Characteristics (T_C=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	Min.	Тур.	Max.
Reverse voltage (DC)	V_{DC}	V	I _R =0.25mA, T _j =25°C	650	-	-
Forward voltage	V _F	٧	I _F =6A, T _j =25°C	-	1.30	1.55
			I _F =6A, T _j =175°C	-	1.65	-
Reverse leakage I _F		4	V _R =650V, T _j =25°C	-	0.5	25
	I _R	μΑ	V _R =650V, T _j =175°C	-	30	-
Total capacitive charge	Q_{C}	nC	V_R =400V, T_j =25°C, QC = $\int_0^{VR}C(V)dV$	-	21.5	-
Total capacitance	C pF		V _R =0V, f=1MHZ	-	382	-
		pF	V _R =200V, f=1MHZ	-	41	-
			V _R =400V, f=1MHZ	-	40	-
Capacitance stored energy	Ec	μJ	V _R =400V	-	3.4	-

■Thermal Characteristics

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	R _{eJ-C}	°C W	1.86





■Typical Characteristics (Typical)

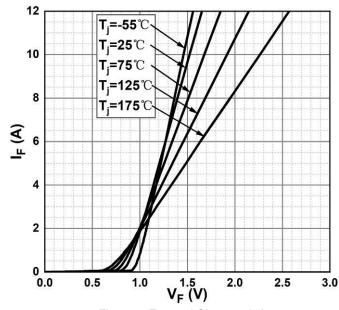


Figure 1. Forward Characteristics

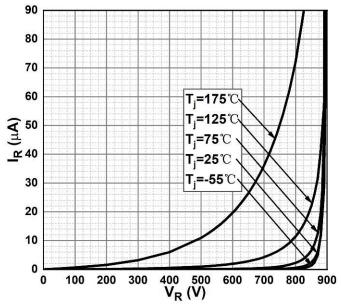


Figure 2. Reverse Characteristic

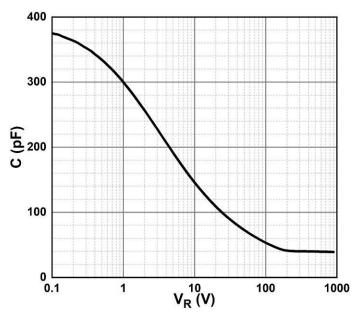


Figure 3. Capacitance vs. Reverse Voltage

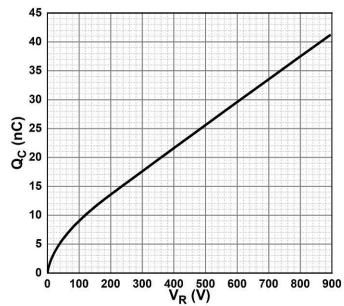
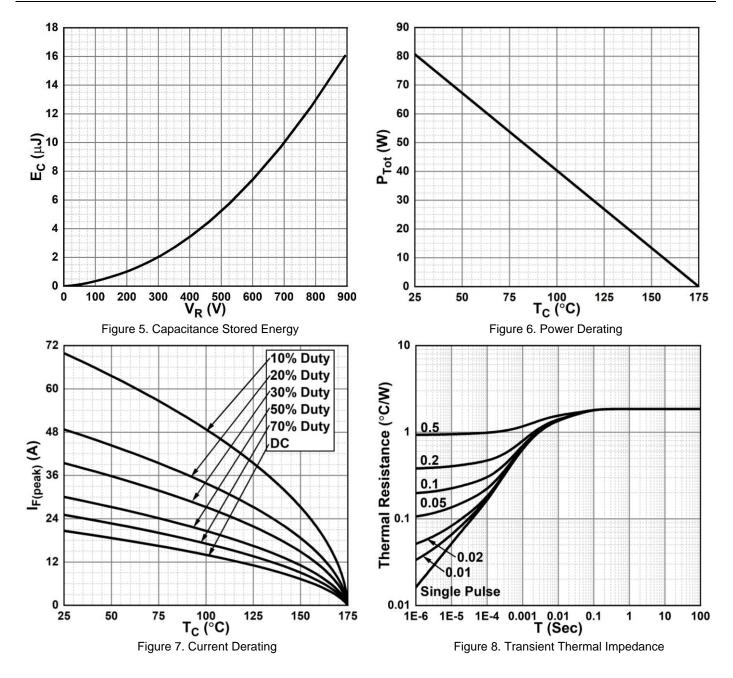


Figure 4. Total Capacitance Charge vs. Reverse Voltage

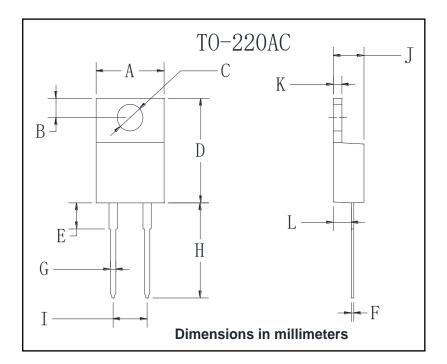








■Outline Dimensions



TO-220AC			
Dim	Min	Max	
Α	9.95	10.35	
В	2.55	2.95	
С	3.75	4.05	
D	14.95	15.25	
Е	3.75	4.25	
F	0.26	0.5	
G	0.68	0.94	
Н	13.3	13.9	
I	4.86	5.26	
J	4.38	4.78	
K	1.14	1.4	
L	2.37	2.79	



YJD106506PYG5

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